

TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC74AC20P, TC74AC20F, TC74AC20FN

DUAL 4-INPUT NAND GATE

(Note) The JEDEC SOP (FN) is not available in Japan.

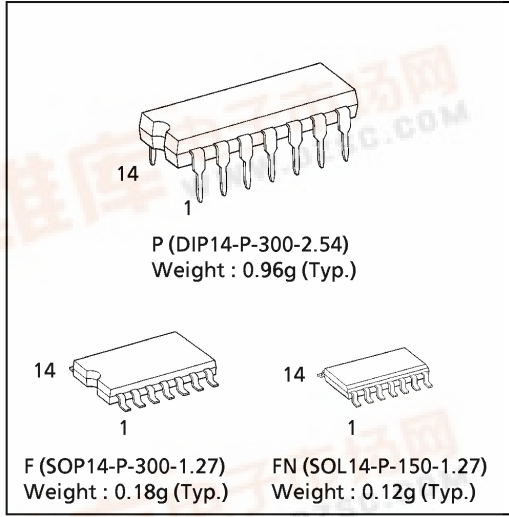
The TC74AC20 is an advanced high speed CMOS 4-INPUT NAND GATE fabricated with silicon gate and double-layer metal wiring C²MOS technology.

It achieves the high speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation.

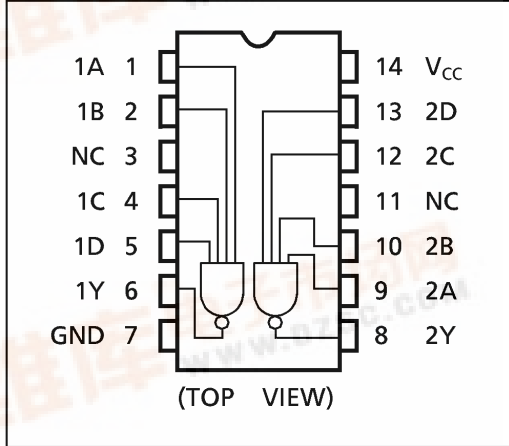
The internal circuit is composed of 3 stages including buffer output, which provide high noise immunity and stable output. All inputs are equipped with protection circuits against static discharge or transient excess voltage.

FEATURES:

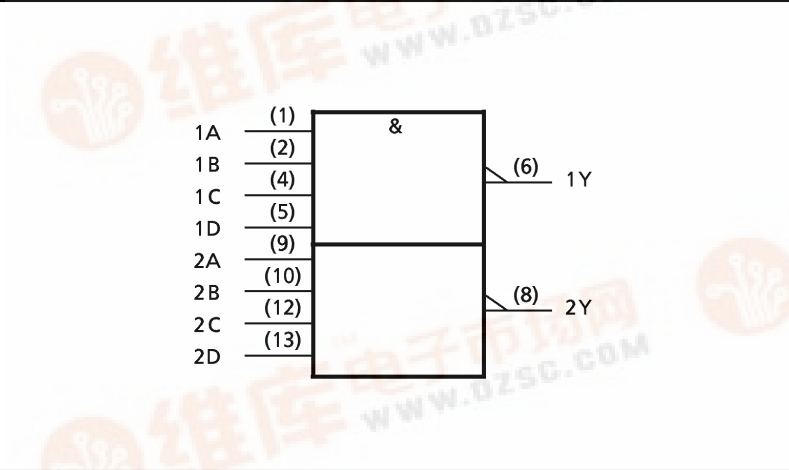
- High Speed..... $t_{pd} = 4.1ns$ (typ.) at $V_{CC} = 5V$
- Low Power Dissipation..... $I_{CC} = 4\mu A$ (Max.) at $T_a = 25^\circ C$
- High Noise Immunity..... $V_{NIH} = V_{NIL} = 28\% V_{CC}$ (Min.)
- Symmetrical Output Impedance... $|I_{OH}| = I_{OL} = 24mA$ (Min.)
Capability of driving 50Ω transmission lines.
- Balanced Propagation Delays..... $t_{pLH} \approx t_{pHL}$
- Wide Operating Voltage Range... $V_{CC} (opr) = 2V \sim 5.5V$
- Pin and Function Compatible with 74F20



PIN ASSIGNMENT



IEC LOGIC SYMBOL



TRUTH TABLE

A	B	C	D	Y
L	X	X	X	H
X	L	X	X	H
X	X	L	X	H
X	X	X	L	H
H	H	H	H	L

X : Don't Care

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ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	V_{CC}	-0.5~7.0	V
DC Input Voltage	V_{IN}	-0.5~ $V_{CC} + 0.5$	V
DC Output Voltage	V_{OUT}	-0.5~ $V_{CC} + 0.5$	V
Input Diode Current	I_{IK}	± 20	mA
Output Diode Current	I_{OK}	± 50	mA
DC Output Current	I_{OUT}	± 50	mA
DC V_{CC} /Ground Current	I_{CC}	± 100	mA
Power Dissipation	P_D	500 (DIP)* / 180 (SOP)	mW
Storage Temperature	T_{stg}	-65~150	°C

*500mW in the range of $T_a = -40^{\circ}\text{C} \sim 65^{\circ}\text{C}$. From $T_a = 65^{\circ}\text{C}$ to 85°C a derating factor of $-10\text{mW}/^{\circ}\text{C}$ should be applied up to 300mW.

RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	V_{CC}	2.0~5.5	V
Input Voltage	V_{IN}	0~ V_{CC}	V
Output Voltage	V_{OUT}	0~ V_{CC}	V
Operating Temperature	T_{opr}	-40~85	°C
Input Rise and Fall Time	dt/dV	0~ 100 ($V_{CC} = 3.3 \pm 0.3\text{V}$) 0~ 20 ($V_{CC} = 5 \pm 0.5\text{V}$)	ns / V

DC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION	V_{CC} (V)	$T_a = 25^{\circ}\text{C}$			$T_a = -40 \sim 85^{\circ}\text{C}$		UNIT	
				MIN.	TYP.	MAX.	MIN.	MAX.		
High - Level Input Voltage	V_{IH}		2.0	1.50	—	—	1.50	—	V	
			3.0	2.10	—	—	2.10	—		
			5.5	3.85	—	—	3.85	—		
Low - Level Input Voltage	V_{IL}		2.0	—	—	0.50	—	0.50	V	
			3.0	—	—	0.90	—	0.90		
			5.5	—	—	1.65	—	1.65		
High - Level Output Voltage	V_{OH}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OH} = -50\mu\text{A}$	2.0	1.9	2.0	—	1.9	—	V
				3.0	2.9	3.0	—	2.9	—	
				4.5	4.4	4.5	—	4.4	—	
			$I_{OH} = -4\text{mA}$ $I_{OH} = -24\text{mA}$ $I_{OH} = -75\text{mA}^*$	3.0	2.58	—	—	2.48	—	
				4.5	3.94	—	—	3.80	—	
5.5	—	—	—	3.85	—					
Low - Level Output Voltage	V_{OL}	$V_{IN} = V_{IH}$	$I_{OL} = 50\mu\text{A}$	2.0	—	0.0	0.1	—	0.1	V
				3.0	—	0.0	0.1	—	0.1	
				4.5	—	0.0	0.1	—	0.1	
			$I_{OL} = 12\text{mA}$ $I_{OL} = 24\text{mA}$ $I_{OL} = 75\text{mA}^*$	3.0	—	—	0.36	—	0.44	
				4.5	—	—	0.36	—	0.44	
5.5	—	—	—	—	1.65					
Input Leakage Current	I_{IN}	$V_{IN} = V_{CC}$ or GND	5.5	—	—	± 0.1	—	± 1.0	μA	
Quiescent Supply Current	I_{CC}	$V_{IN} = V_{CC}$ or GND	5.5	—	—	4.0	—	40.0		

* : This spec indicates the capability of driving 50Ω transmission lines.
One output should be tested at a time for a 10ms maximum duration.

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AC ELECTRICAL CHARACTERISTICS ($C_L = 50\text{pF}$, $R_L = 500\Omega$, Input $t_r = t_f = 3\text{ns}$)

PARAMETER	SYMBOL	TEST CONDITION	Ta = 25°C			Ta = -40~85°C		UNIT	
			V _{CC} (V)	MIN.	TYP.	MAX.	MIN.		MAX.
Propagation Delay Time	t _{pLH}		3.3 ± 0.3	—	6.0	10.0	1.0	11.4	ns
	t _{pHL}		5.0 ± 0.5	—	4.8	7.0	1.0	8.0	
Input Capacitance	C _{IN}		—	5	10	—	10	pF	
Power Dissipation Capacitance	C _{PD} (1)		—	66	—	—	—		

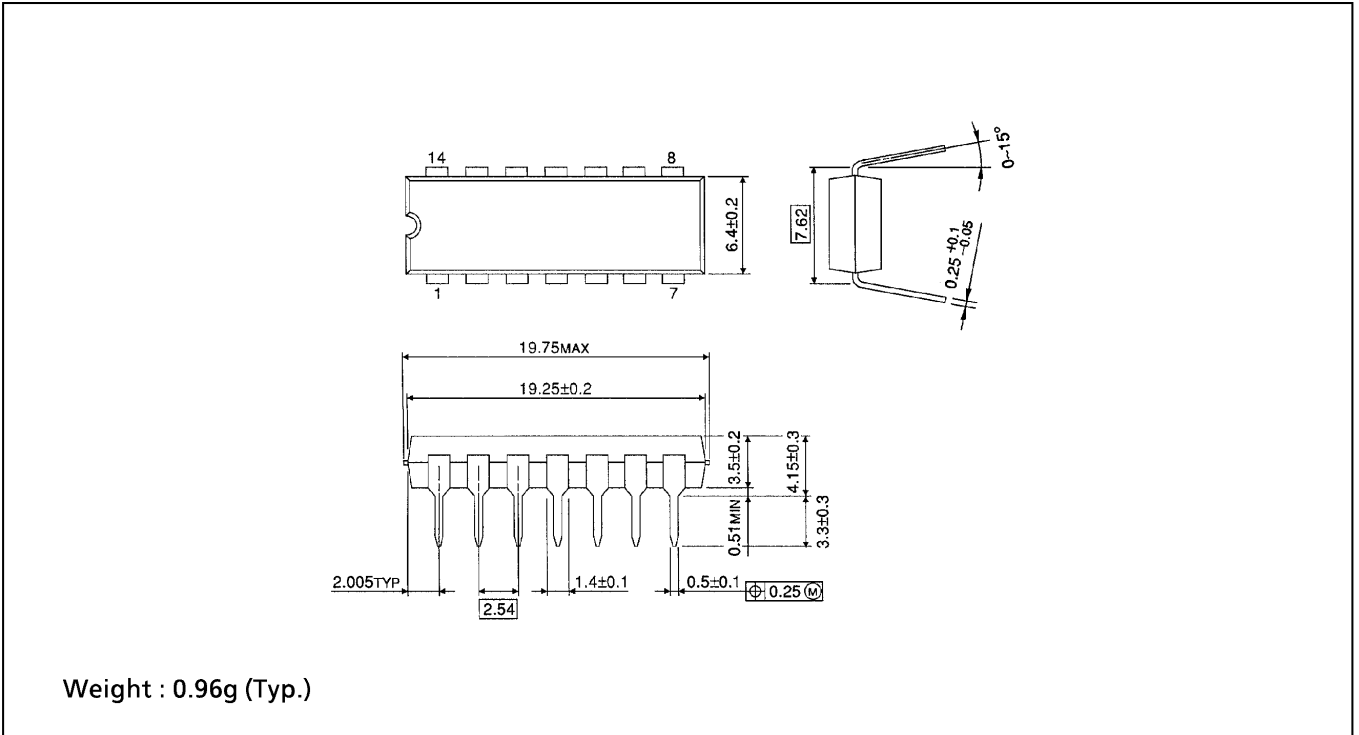
Note(1) C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation :

$$I_{CC}(\text{opr.}) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC} / 2 \text{ (per Gate)}$$

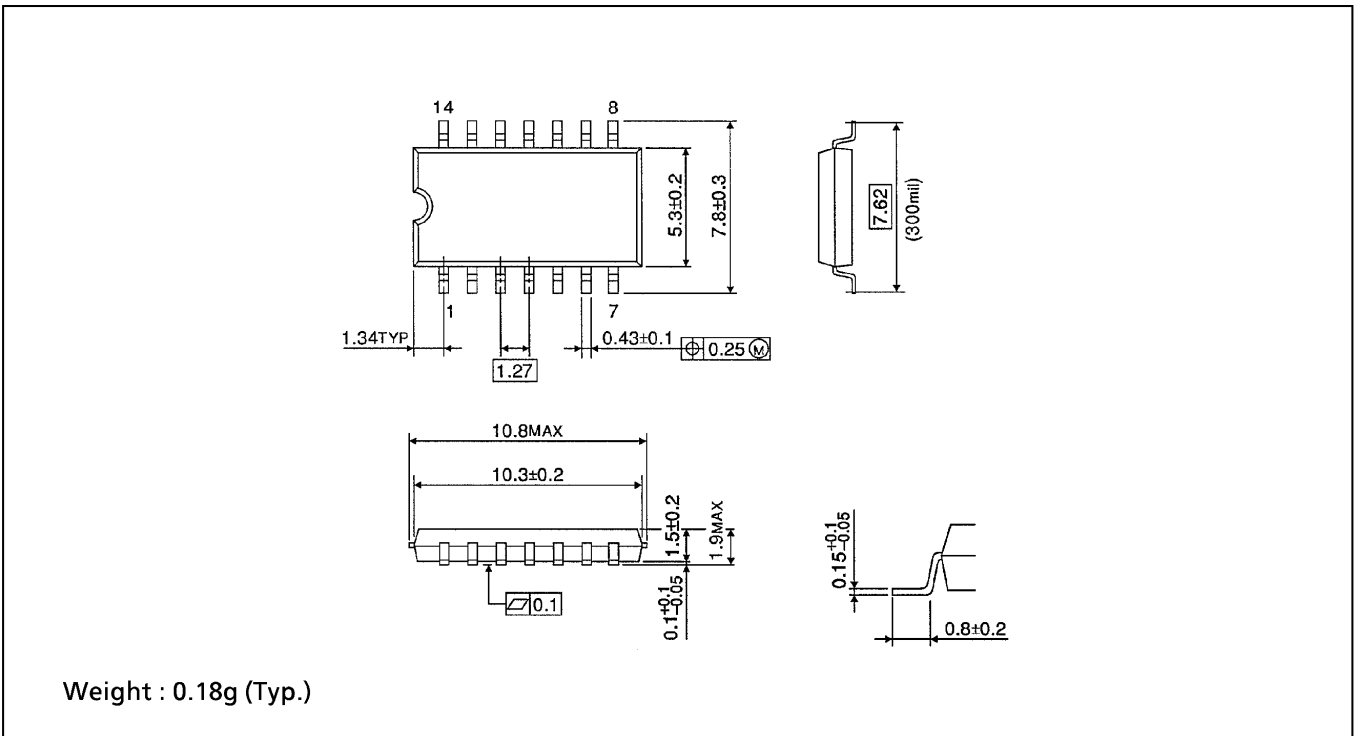
DIP 14PIN OUTLINE DRAWING (DIP14-P-300-2.54)

Unit in mm



SOP 14PIN (200mil BODY) OUTLINE DRAWING (SOP14-P-300-1.27)

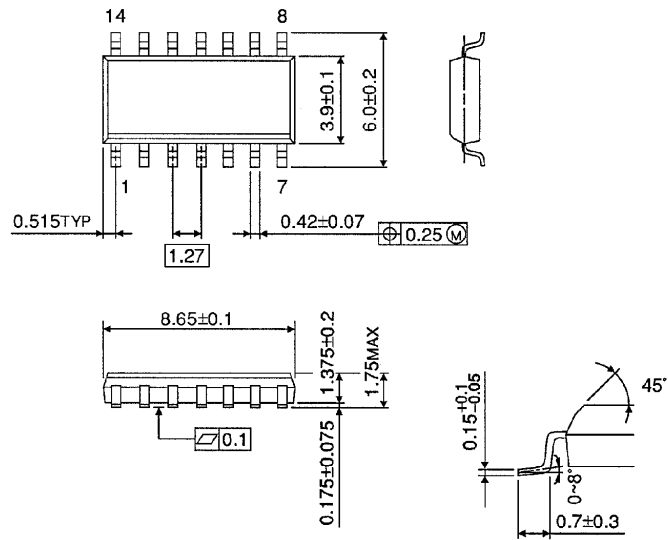
Unit in mm



SOP 14PIN (150mil BODY) OUTLINE DRAWING (SOL14-P-150 -1.27)

Unit in mm

(Note) This package is not available in Japan.



Weight : 0.12g (Typ.)